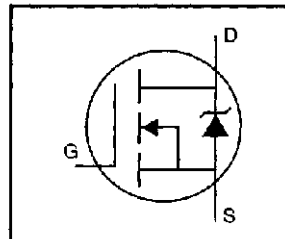


# IRFBF30PbF

## HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead-Free

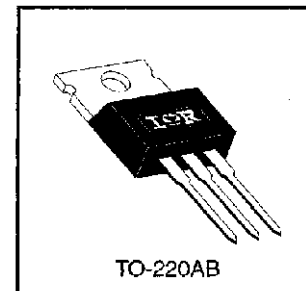


$V_{DSS} = 900V$
$R_{DS(on)} = 3.7\Omega$
$I_D = 3.6A$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	3.6	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	2.3	
$I_{DM}$	Pulsed Drain Current ①	14	
$P_D @ T_C = 25^\circ C$	Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	250	mJ
$I_{AR}$	Avalanche Current ①	3.6	A
$E_{AR}$	Repetitive Avalanche Energy ①	13	mJ
dv/dt	Peak Diode Recovery dv/dt ③	1.5	V/ns
$T_J$	Operating Junction and Storage Temperature Range	-55 to +150	°C
$T_{STG}$			
	Mounting Torque, 6-32 or M3 screw	10 lbf·in (1.1 N·m)	


### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

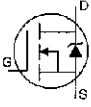
# IRFBF30PbF

International  
IR Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

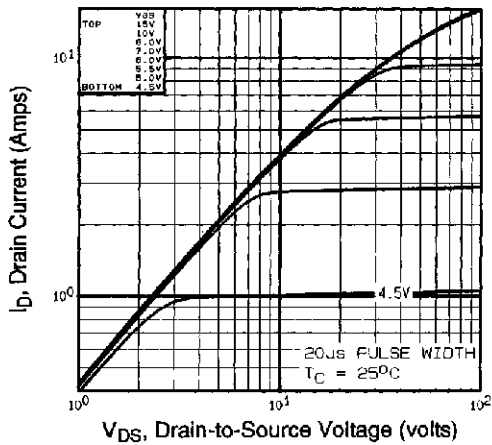
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	900	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	1.1	—	V/°C	Reference to $25^\circ\text{C}, I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	3.7	$\Omega$	$V_{GS}=10V, I_D=2.2A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$g_{fs}$	Forward Transconductance	2.3	—	—	S	$V_{DS}=100V, I_D=2.2A$ ④
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	100	$\mu A$	$V_{DS}=900V, V_{GS}=0V$
		—	—	500		$V_{DS}=720V, V_{GS}=0V, T_J=125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-20V$
$Q_g$	Total Gate Charge	—	—	78	nC	$I_D=3.6A$
$Q_{gs}$	Gate-to-Source Charge	—	—	10		$V_{DS}=360V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	42		$V_{GS}=10V$ See Fig. 6 and 13 ②
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD}=450V$
$t_r$	Rise Time	—	25	—		$I_D=3.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	90	—		$R_G=12\Omega$
$t_f$	Fall Time	—	30	—		$R_D=120\Omega$ See Figure 10 ②
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	1200	—	pF	$V_{GS}=0V$
$C_{oss}$	Output Capacitance	—	320	—		$V_{DS}=25V$
$C_{rss}$	Reverse Transfer Capacitance	—	200	—		$f=1.0\text{MHz}$ See Figure 5

## Source-Drain Ratings and Characteristics

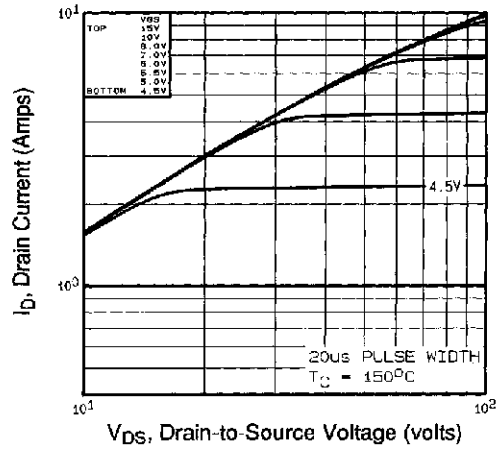
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	3.6	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	14		
$V_{SD}$	Diode Forward Voltage	—	—	1.8	V	$T_J=25^\circ\text{C}, I_S=3.6A, V_{GS}=0V$ ④
$t_{rr}$	Reverse Recovery Time	—	430	650	ns	$T_J=25^\circ\text{C}, I_F=3.6A$
$Q_{rr}$	Reverse Recovery Charge	—	1.4	2.1	$\mu C$	$di/dt=100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

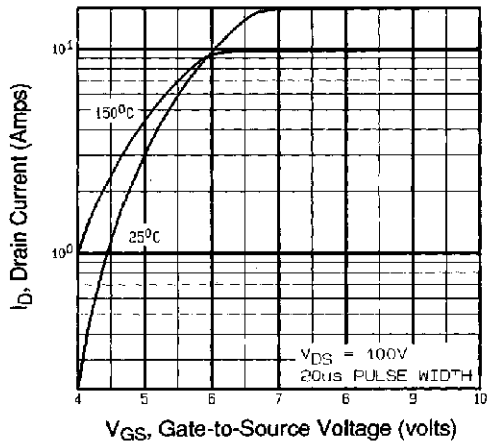
- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ②  $V_{DD}=50V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=36\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=3.6A$  (See Figure 12)
- ③  $I_{SD}\leq 3.6A$ ,  $di/dt\leq 70A/\mu s$ ,  $V_{DD}\leq 600V$ ,  $T_J\leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



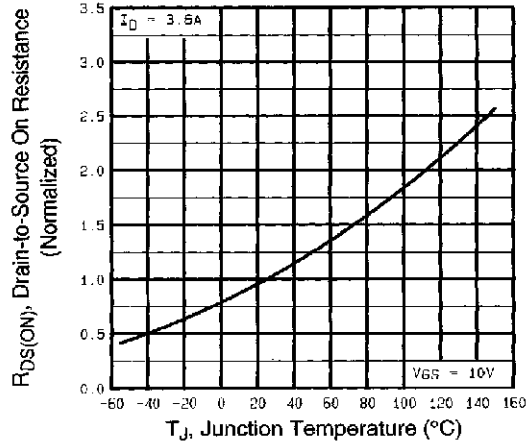
**Fig 1.** Typical Output Characteristics,  
 $T_C=25^\circ\text{C}$



**Fig 2.** Typical Output Characteristics,  
 $T_C=150^\circ\text{C}$



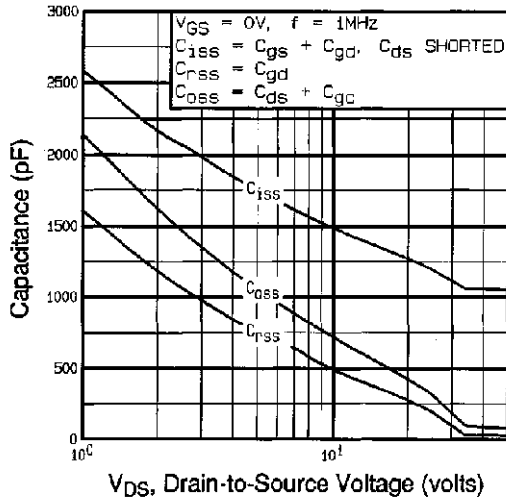
**Fig 3.** Typical Transfer Characteristics



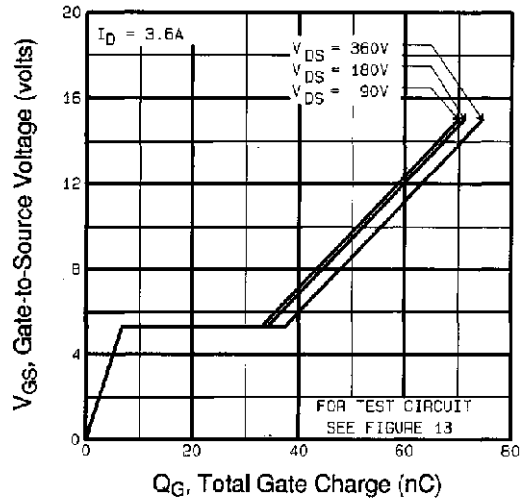
**Fig 4.** Normalized On-Resistance  
 Vs. Temperature

# IRFBF30PbF

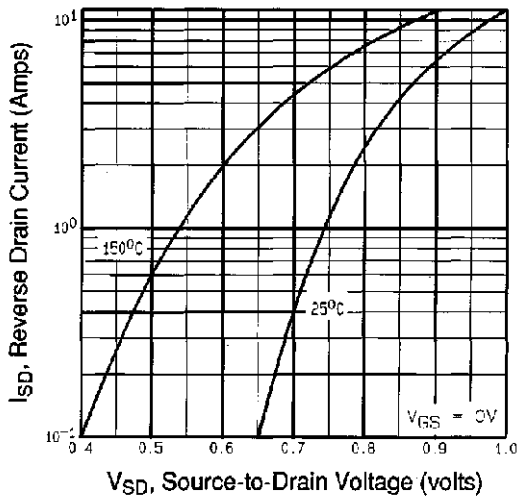
International  
IR Rectifier



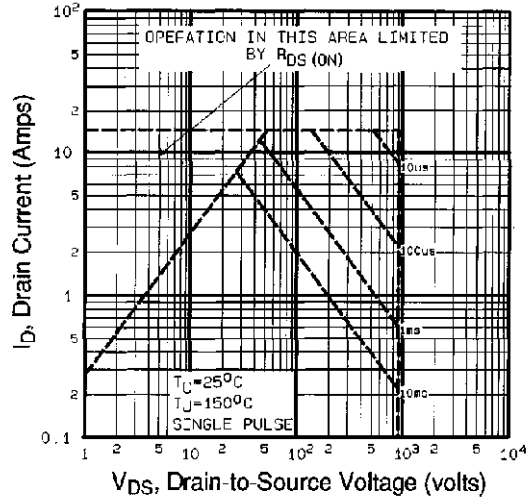
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



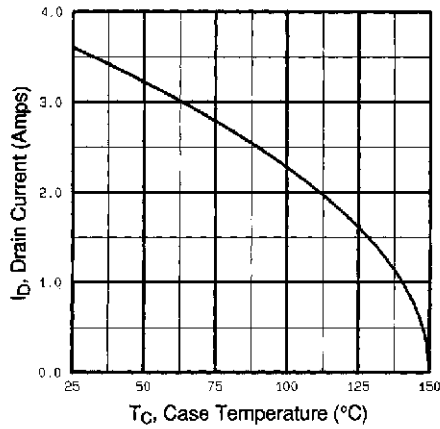
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



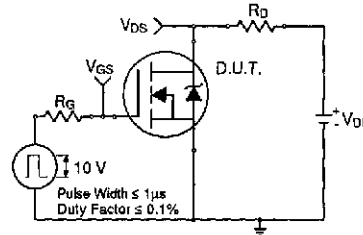
**Fig 7.** Typical Source-Drain Diode Forward Voltage



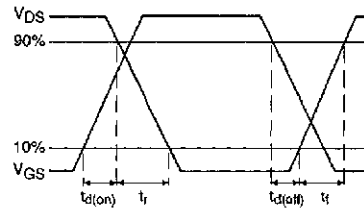
**Fig 8.** Maximum Safe Operating Area



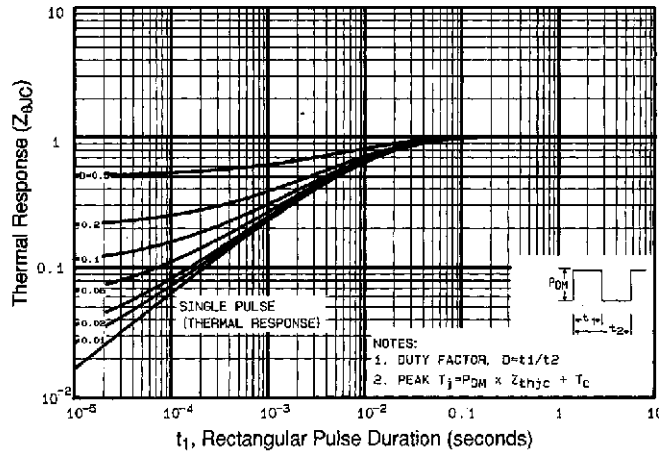
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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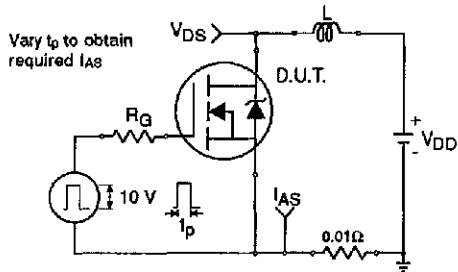


Fig 12a. Unclamped Inductive Test Circuit

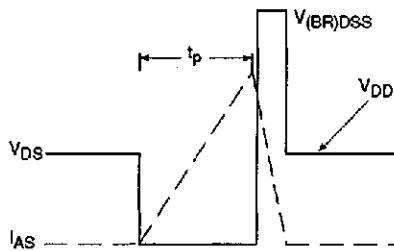


Fig 12b. Unclamped Inductive Waveforms

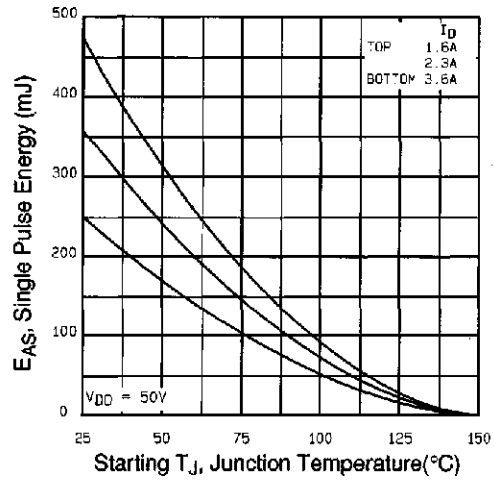


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

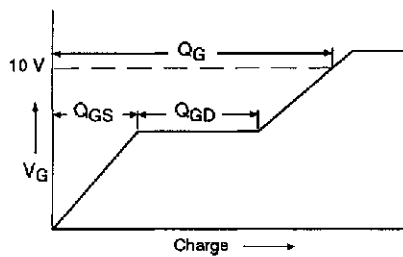


Fig 13a. Basic Gate Charge Waveform

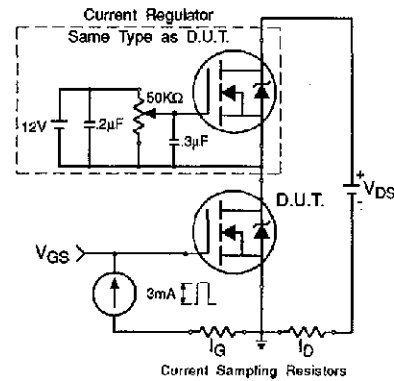
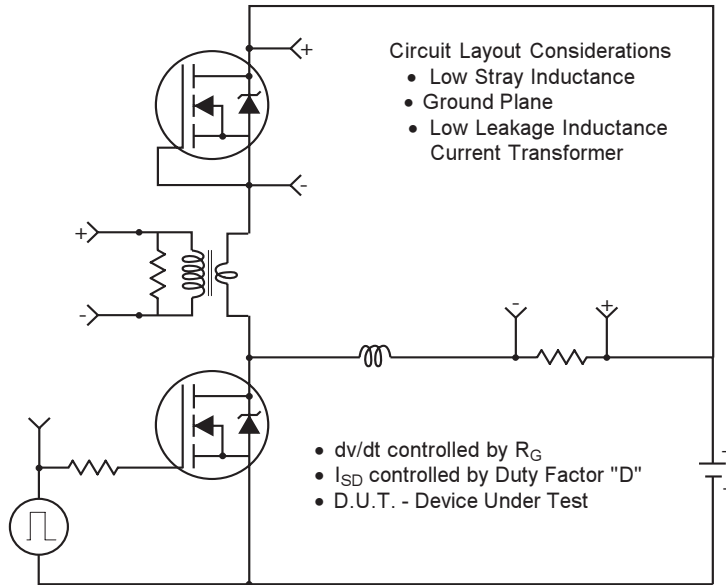
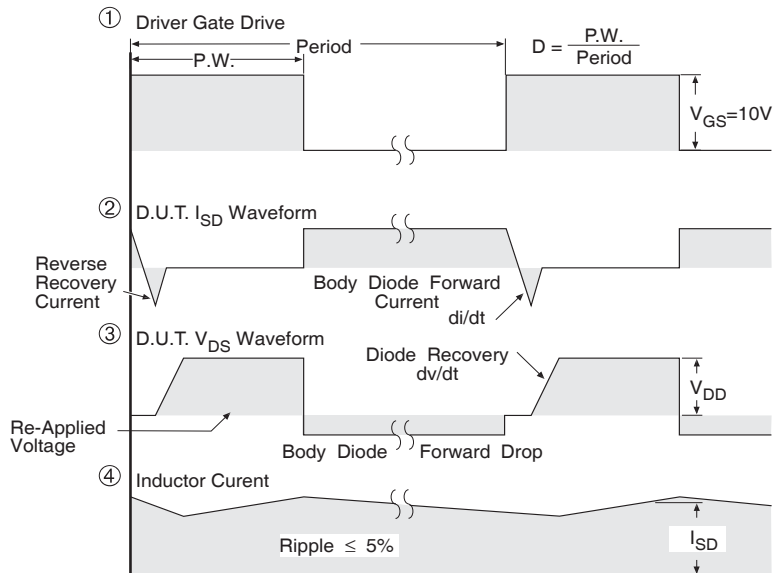


Fig 13b. Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



- \* Reverse Polarity for P-Channel
- \*\* Use P-Channel Driver for P-Channel Measurements



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

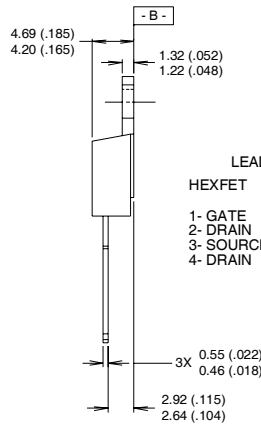
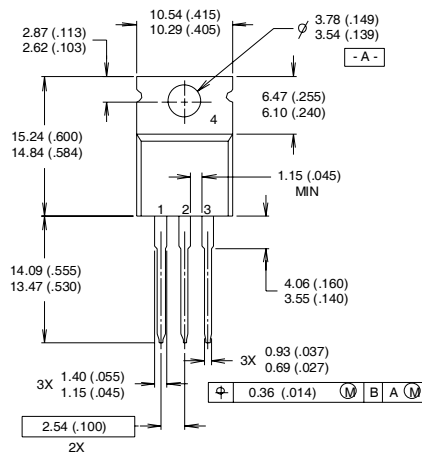
**Fig. 14** For N and P Channel HEXFETS

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## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



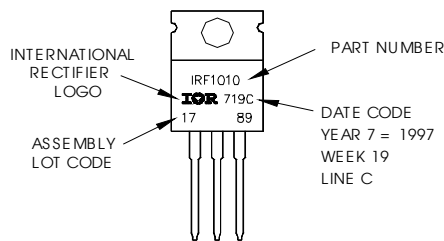
LEAD ASSIGNMENTS	
HEXFET	IGBTs, CoPACK
1- GATE	1- GATE
2- DRAIN	2- COLLECTOR
3- SOURCE	3- EMITTER
4- DRAIN	4- COLLECTOR

**NOTES:**

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.



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 TAC Fax: (310) 252-7903  
 08/04

Document Number: 91122

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